

Small Signal MOSFET

60 V, 340 mA, Single, N-Channel, SC-70

Features

- ESD Protected
- Low $R_{DS(on)}$
- Small Footprint Surface Mount Package
- This is a Pb-Free Device

Applications

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter
- Portable Applications i.e. DSC, PDA, Cell Phone, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Drain Current (Note 1) Steady State	I_D	$T_A = 25^\circ\text{C}$ 310	mA
		$T_A = 85^\circ\text{C}$ 220	
$t < 5$ s		$T_A = 25^\circ\text{C}$ 340	mA
		$T_A = 85^\circ\text{C}$ 240	
Power Dissipation (Note 1) Steady State $t < 5$ s	P_D	280 330	mW
Pulsed Drain Current ($t_p = 10$ μs)	I_{DM}	1.4	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to $+150$	$^\circ\text{C}$
Source Current (Body Diode)	I_S	250	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$
Gate-Source ESD Rating (HBM, Method 3015)	ESD	900	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	450	$^\circ\text{C/W}$
Junction-to-Ambient - $t \leq 5$ s (Note 1)	$R_{\theta JA}$	375	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)

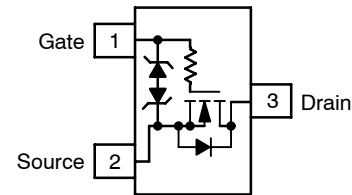


ON Semiconductor®

<http://onsemi.com>

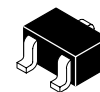
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX (Note 1)
60 V	1.6 Ω @ 10 V	340 mA
	2.5 Ω @ 4.5 V	

Simplified Schematic

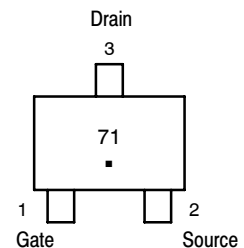


(Top View)

MARKING DIAGRAM & PIN ASSIGNMENT



SC-70/SOT-323
CASE 419
STYLE 8



71 = Device Code
▪ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
2N7002WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2N7002W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
-----------	--------	----------------	-----	-----	-----	-------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			71		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V	T _J = 25°C		1	μA
			T _J = 125°C		500	μA
		V _{GS} = 0 V, V _{DS} = 50 V	T _J = 25°C		100	nA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±10	μA
		V _{DS} = 0 V, V _{GS} = ±10 V			450	nA
		V _{DS} = 0 V, V _{GS} = ±5.0 V			150	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0		2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			4.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 500 mA		1.19	1.6	Ω
		V _{GS} = 4.5 V, I _D = 200 mA		1.33	2.5	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 200 mA		80		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 20 V		24.5		pF
Output Capacitance	C _{OSS}			4.2		
Reverse Transfer Capacitance	C _{RSS}			2.2		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V; I _D = 200 mA		0.7		nC
Threshold Gate Charge	Q _{G(TH)}			0.1		
Gate-to-Source Charge	Q _{GS}			0.3		
Gate-to-Drain Charge	Q _{GD}			0.1		

SWITCHING CHARACTERISTICS, V_{GS} = V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DD} = 25 V, I _D = 500 mA, R _G = 25 Ω		12.2		ns
Rise Time	t _r			9.0		
Turn-Off Delay Time	t _{d(OFF)}			55.8		
Fall Time	t _f			29		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 200 mA	T _J = 25°C		0.8	1.2	V
			T _J = 85°C		0.7		

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%
- Switching characteristics are independent of operating junction temperatures

[查询"2N7002W-D"供应商](#)

TYPICAL CHARACTERISTICS

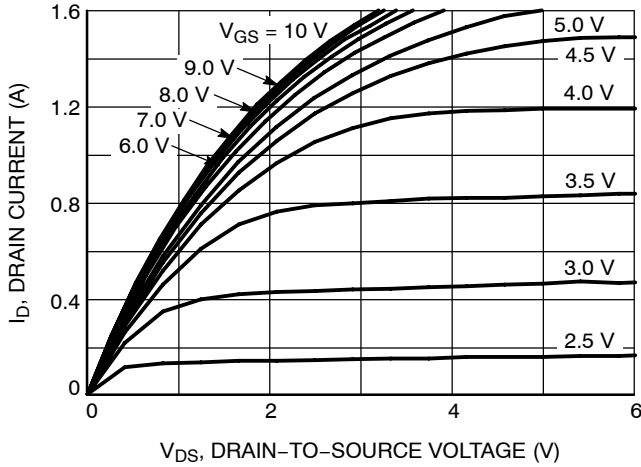


Figure 1. On-Region Characteristics

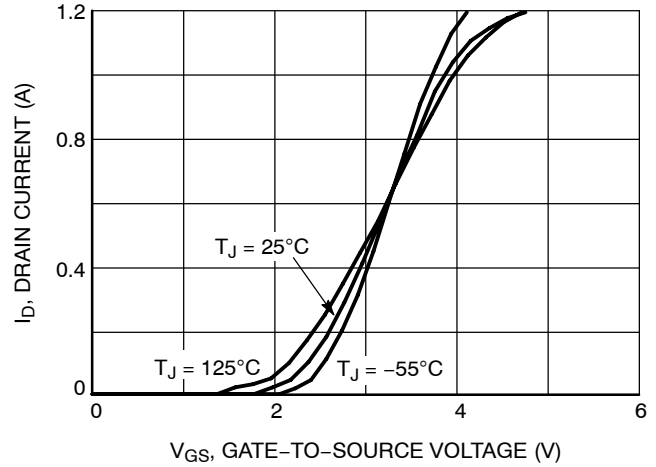


Figure 2. Transfer Characteristics

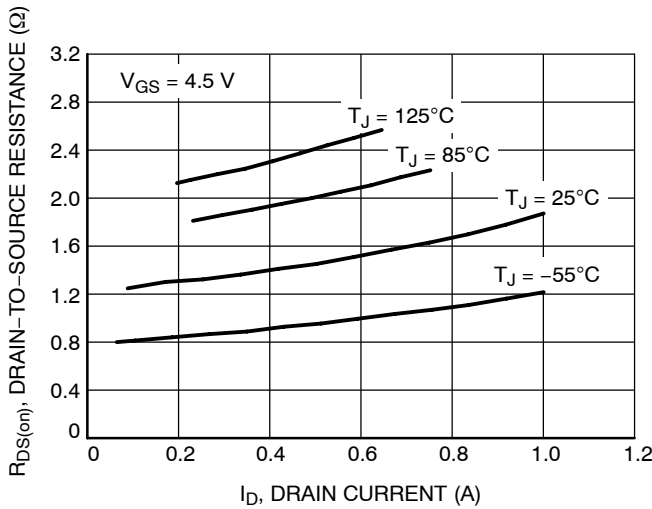


Figure 3. On-Resistance vs. Drain Current and Temperature

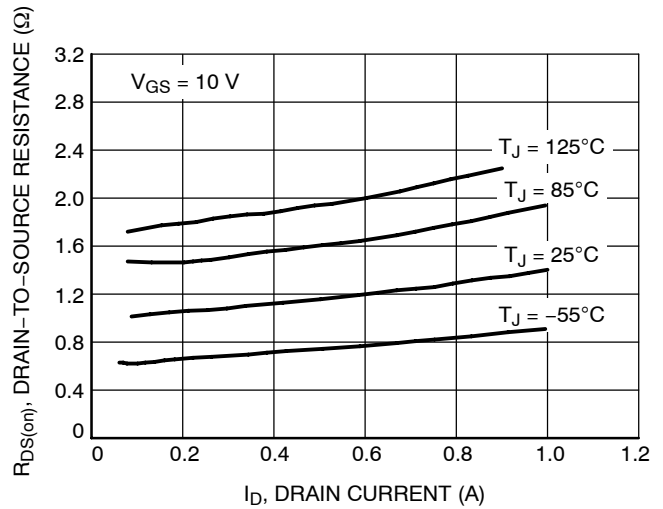


Figure 4. On-Resistance vs. Drain Current and Temperature

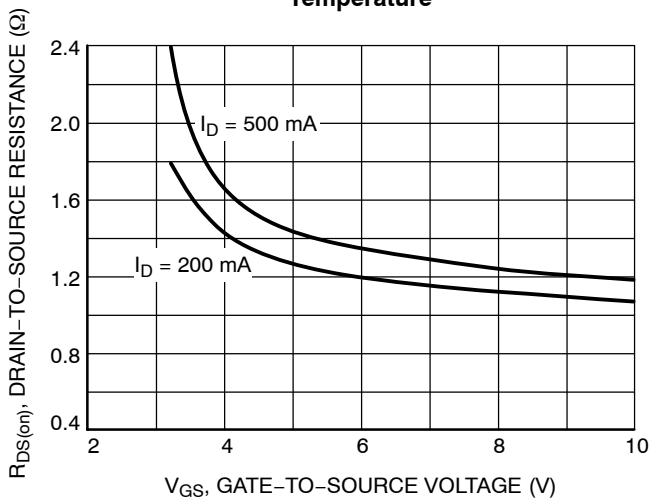


Figure 5. On-Resistance vs. Gate-to-Source Voltage

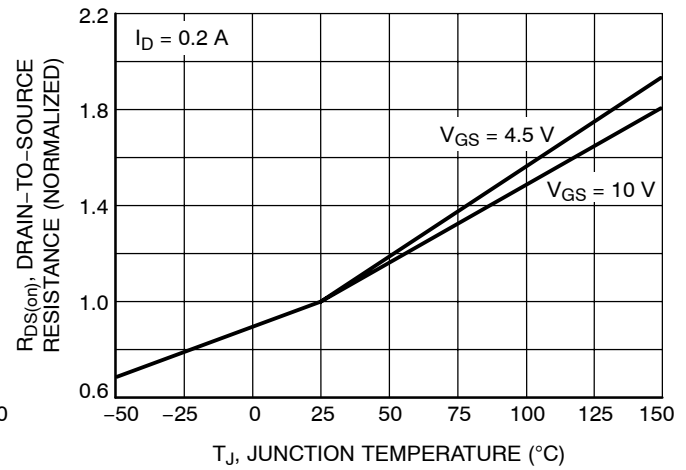


Figure 6. On-Resistance Variation with Temperature

[查询"2N7002W-D"供应商](#)

TYPICAL CHARACTERISTICS

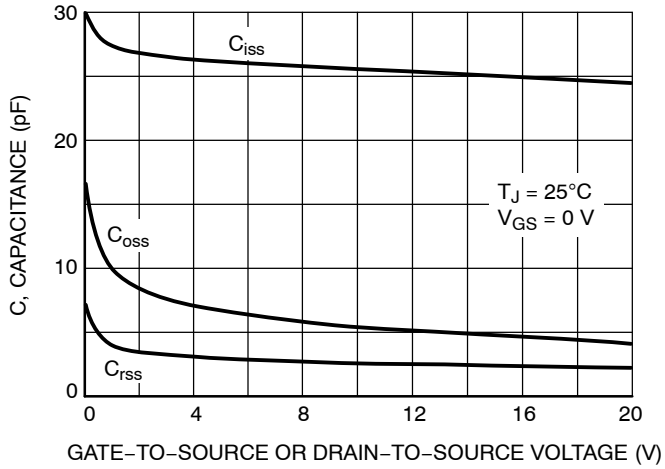


Figure 7. Capacitance Variation

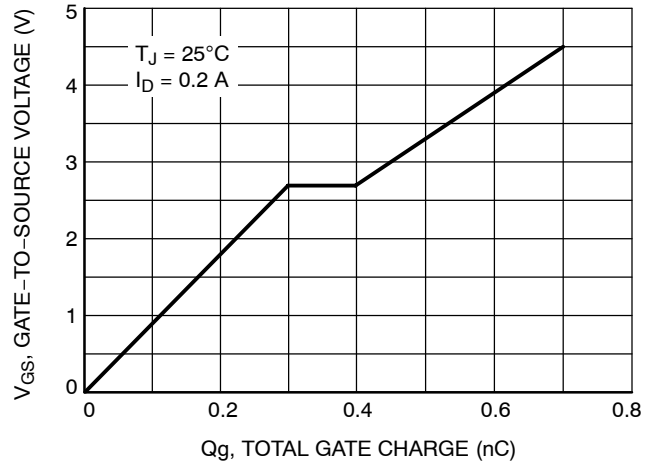


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

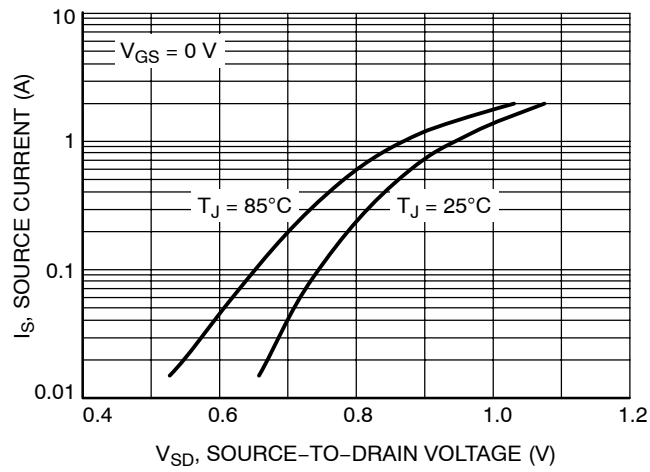


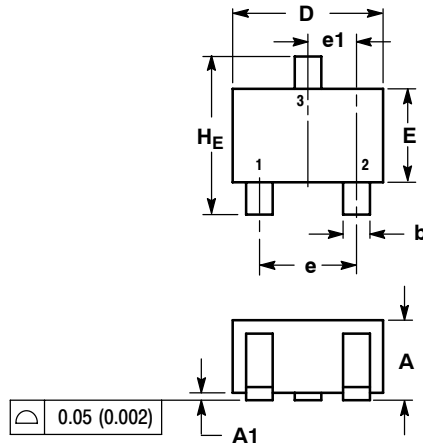
Figure 9. Diode Forward Voltage vs. Current

2N7002W

[查询"2N7002W-D"供应商](#)

PACKAGE DIMENSIONS

SC-70 (SOT-323)
CASE 419-04
ISSUE M

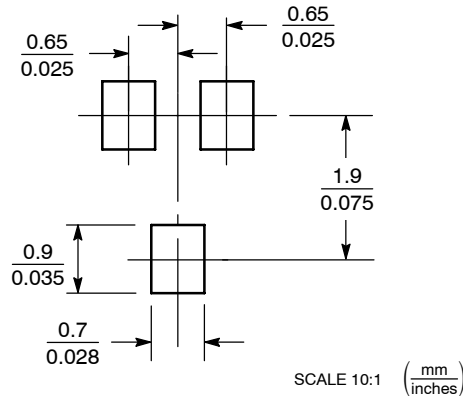


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>
Order Literature: <http://www.onsemi.com/litorder>
For additional information, please contact your local Sales Representative.